

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

NISHIMOTO et al

Serial No.: 08/897,839

Filed: July 21, 1997

For: STRESS-ADJUSTED INSULATING
FILM FORMING METHOD,
SEMICONDUCTOR DEVICE AND
METHOD OF MANUFACTURING THE
SAME

Group Art Unit: 2814

Examiner: K. Eaton

VIA FACSIMILE

703 308 7755

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MAY 23 2000

TECHNOLOGY CENTER 2800

SUPPLEMENTAL AMENDMENT IN RESPONSE
TO OFFICE ACTION OF FEBRUARY 3, 2000

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Supplemental to Applicants' response filed May 3, 2000,
please amend the captioned application as follows:

IN THE SPECIFICATION:

Page 7, line 7, change "dyne/cm²" to read --dyne/cm--; and
line 8, after "experiment" insert --, a value obtained
by multiplying the stress in a layer (in dynes/cm²) by the
thickness of that layer, and accumulated for all layers--.

Page 12, line 12, change "dyne/cm²" to read --dyne/cm--.

Page 13, line 12, change "dyne/cm²" to read --dyne/cm--.

Page 20, line 21, change "dyne/cm²" to read --dyne/cm--.

Page 21, line 19, change "dyne/cm²" to read --dyne/cm--; and
line 21, change "dyne/cm²" to read --dyne/cm--.

NE
Wrong
page & line